

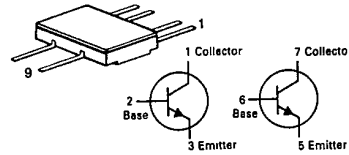
6367254 MOTOROLA SC (XSTRS/R F)

96D 82391 D

J-29-27

**2N3043
thru
2N3045
2N3048**

CASE 610A-04, STYLE 1



**DUAL
AMPLIFIER TRANSISTOR**

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	45	Vdc
Collector-Base Voltage	V _{CBO}	45	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current — Continuous	I _C	30	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	One Die	250
		Both Dies	350
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	One Die	0.7
		Both Dies	1.4
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	45	—	Vdc
Emitter-Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	5.0	—	Vdc
Collector Cutoff Current (V _{CB} = 45 Vdc, I _E = 0) (V _{CB} = 45 Vdc, I _E = 0, T _A = +150°C)	I _{CBO}	—	0.010 10	μAdc
Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)	I _{EBO}	—	0.010	μAdc
ON CHARACTERISTICS				
DC Current Gain(1) (I _C = 10 μAdc, V _{CE} = 5.0 Vdc)	h _{FE}	2N3043, 2N3044, 2N3045 2N3048	100 50	300 200
		2N3043, 2N3044, 2N3045 2N3048	130 65	—
Collector-Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 0.5 mAdc)	V _{CE(sat)}	—	1.0	Vdc
Base-Emitter On Voltage (I _C = 10 mAdc, V _{CE} = 5.0 Vdc)	V _{BE}	0.6	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 20 MHz)	f _T	30	—	MHz
Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	—	8.0	pF
Input Impedance (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 1.0 kHz)	h _{ie}	2N3043, 2N3044, 2N3045 2N3048	3.2k 1.6k	19k 13k
		2N3043, 2N3044, 2N3045 2N3048	130 65	600 400
Small-Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 1.0 kHz)	h _{fe}	—	—	—
Output Admittance (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 1.0 kHz)	h _{oe}	—	100	—
		—	70	—
Noise Figure (I _C = 10 μAdc, V _{CE} = 5.0 Vdc, R _S = 10 kohms, Bandwidth = 10 Hz to 15.7 kHz)	NF	—	5.0	dB

MOTOROLA SMALL-SIGNAL SEMICONDUCTORS

6367254 MOTOROLA SC (XSTRS/R F)

96D 82392 D

2N3043 thru 2N3045, 2N3048

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ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
MATCHING CHARACTERISTICS				
DC Current Gain Ratio(2) ($I_C = 10 \mu\text{A}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE1}/h_{FE2}	0.9 0.8	1.0 1.0	—
Base-Emitter Voltage Differential ($I_C = 10 \mu\text{A}$, $V_{CE} = 5.0 \text{ Vdc}$)	$ V_{BE1} - V_{BE2} $	— —	5.0 10	mVdc
Base-Emitter Voltage Differential Temperature Gradient ($I_C = 10 \mu\text{A}$, $V_{CE} = 5.0 \text{ Vdc}$, $T_A = -55$ to $+125^\circ\text{C}$)	$\frac{\Delta(V_{BE1} - V_{BE2})}{\Delta T_A}$	— —	10 20	$\mu\text{V}/^\circ\text{C}$

(1) Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.
 (2) The lowest h_{FE} reading is taken as h_{FE1} for this test.

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6367254 MOTOROLA SC (XSTRS/R F)

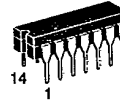
96D 82412 D

T-43-25

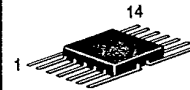
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	60	V _{dc}
Collector-Base Voltage	V _{CB}	60	V _{dc}
Emitter-Base Voltage	V _{EB}	5.0	V _{dc}
Collector Current — Continuous	I _C	600	mAdc
		Each Transistor	Total Device
M558-01 Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	0.525 3.0	1.5 8.57 Watts mW/°C
M558-02 Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	0.14 0.8	0.4 2.29 Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

**M558-01
M558-02**



**M558-01
CERAMIC
CASE 632-02
STYLE 1**



**M558-02
CERAMIC
CASE 607-04
STYLE 1**

**QUAD
TRANSISTORS
PNP SILICON**

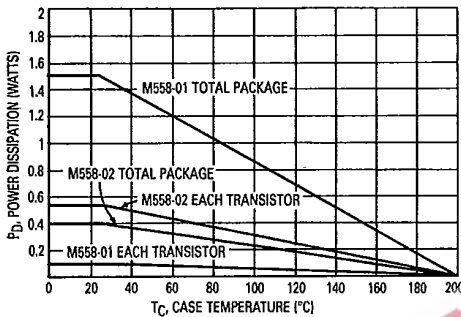


Figure 1. Power Temperature Derating Curve

Table 1. Product Classifications

JAN — Controlled Lot with Sample Environmental and Life Testing
 JTX — 100% Processing Plus Sample Environmental and Life Testing
 JTXV — Same as JTX Plus 100% Internal Visual Inspection

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I _C = 10 mAdc, I _B = 0)	V(BR)CEO	60	—	V _{dc}
Collector-Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	V(BR)CBO	60	—	V _{dc}
Emitter-Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V(BR)EBO	5.0	—	V _{dc}
Collector Cutoff Current (I _E = 0, V _{CB} = 60 Vdc) (I _E = 0, V _{CB} = 60 V, T _A = 150°C)	I _{CBO}	—	10 10	nAdc μA
Emitter Cutoff Current (I _C = 0, V _{CB} = 4.0 Vdc)	I _{EBO}	—	10	nAdc
ON CHARACTERISTICS				
DC Current Gain(1) (I _C = 0.1 mA, V _{CE} = 10 Vdc) (I _C = 1.0 mA, V _{CE} = 10 Vdc) (I _C = 10 mAdc, V _{CE} = 10 Vdc) (I _C = 150 mAdc, V _{CE} = 10 Vdc) (I _C = 500 mAdc, V _{CE} = 10 Vdc) (I _C = 10 mA, V _{CE} = 10 V, T _A = -55°C)	h _{FE}	75 100 100 100 50 50	— 450 — 300 — —	
Collector-Emitter Saturation Voltage (I _C = 150 mAdc, I _B = 15 mAdc) (I _C = 500 mAdc, I _B = 60 mAdc)	V _{CE(sat)}	—	0.4 1.6	V _{dc}
Base-Emitter Saturation Voltage (I _C = 150 mAdc, I _B = 15 mAdc) (I _C = 500 mAdc, I _B = 60 mAdc)	V _{BE(sat)}	0.6	1.3 2.6	V _{dc}
DYNAMIC CHARACTERISTICS				
Current-Gain — Bandwidth Product(1) (I _C = 50 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	250	800	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	—	8.0	pF
Input Capacitance (V _{BE} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	—	30	pF

T-43-25

M558-01, M558-02

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS				
Turn-On Time (V _{CC} = 30 Vdc, V _{BE(off)} = 0.5 Vdc, I _C = 150 mA, I _{B1} = 15 mA) (Figure 2)	t _{on}	—	45	ns
Turn-Off Time (V _{CC} = 30 Vdc, I _C = 150 mA, I _{B1} = I _{B2} = 15 mA) (Figure 3)	t _{off}	—	300	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.

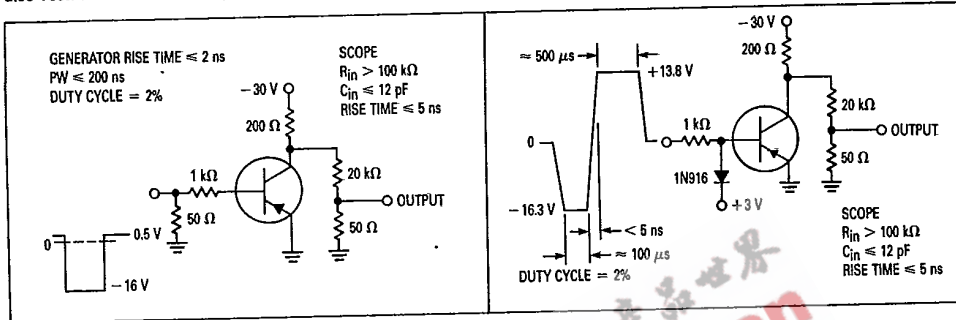


Figure 2. t_{on} Test Circuit

Figure 3. t_{off} Test Circuit

Table 2. JTX, JTXV 100% Processing Steps

	JTX	JTXV
Internal Visual (Mil-Std-750, Method 2072)	—	100%
High Temperature Storage (Mil-Std-750, Method 1032)	100%	100%
Thermal Shock (Mil-Std-750, Method 1051 Cond. F*)	100%	100%
Constant Acceleration (Mil-Std-750, Method 2006, 20 KG ^s , Y ₁)	100%	100%
Hermetic Seal (Fine + Gross Leak) (Mil-Std-750, Method 1071, Cond. G or H)**	100%	100%
READ Electrical Parameters (Group A)	100%	100%
High Temperature Reverse Bias (Mil-Std-750, Method 1039, Cond. A)	100%	100%
READ Electrical Parameters (Group A)	100%	100%
Power Burn-In (Mil-Std-750, Method 1039, Cond. B)	100%	100%
READ Electrical Parameters (Group A)	100%	100%

*T_(LOW) = -55°C
**Cond. G, Fine Leak = 1 x 10⁻⁷ ATM. CC/sec.

Table 3. Simplified Hi-Rel Product Flow

JAN	JTX	JTXV
Commercial Product	Commercial Product	100% Pre Cap Visual
↓	↓	↓
Group A, B, C Sample Test	100% Test	100% Test
↓	↓	↓
Ship	Group A, B, C Sample Test	Group A, B, C Sample Test
	↓	↓
	Ship	Ship

